

Transistors

General purpose (dual transistors)

FMS3 / FMS4 / IMT4

●Features

- 1) Two 2SA1514K chips in an AMT package.
- 2) High breakdown voltage.

●Absolute maximum ratings (Ta=25°C)

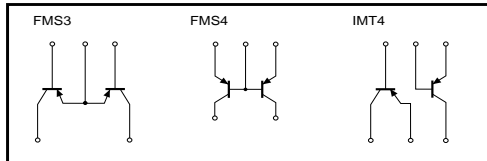
Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	-120	V
Collector-emitter voltage	V _{CE0}	-120	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _c	-50	mA
Power dissipation	P _c	300 (TOTAL)	mW *
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55→150	°C

*200mW per element must not be exceeded.

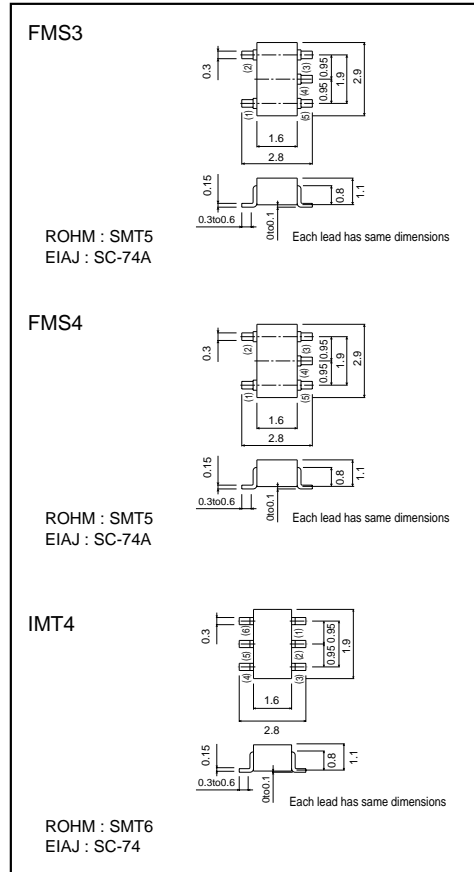
●Package, marking, and Packaging specifications

Part No.	FMS3	FMS4	IMT4
Package	SMT5	SMT5	SMT6
Marking	S3	S4	T4
Code	T148	T148	T108
Basic ordering unit (pieces)	3000	3000	3000

●Circuit diagram



●External dimensions (Units : mm)



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	-120	-	-	V	I _c =-50μA
Collector-emitter breakdown voltage	BV _{CE0}	-120	-	-	V	I _c =-1mA
Emitter-base breakdown voltage	BV _{EB0}	-5	-	-	V	I _E =-50μA
Collector cutoff current	I _{cbo}	-	-	-0.5	μA	V _{CB} =-100V
Emitter cutoff current	I _{EBO}	-	-	-0.5	μA	V _{EB} =-4V
DC current transfer ratio	h _{FE}	180	-	820	-	V _{CE} =-6V, I _c =2mA
Transition frequency	f _r	-	140	-	MHz	V _{CE} =-12V, I _E =2mA, f=100MHz *
Collector-emitter saturation voltage	V _{CE(sat)}	-	-	-0.5	V	I _c /I _E =-10mA/-1mA

*Transition frequency of the device.